

650V / 2A
N-Channel Enhancement Mode MOSFET

650V, $R_{DS(ON)}=4.6\Omega@V_{GS}=10V, I_D=1A$

Features

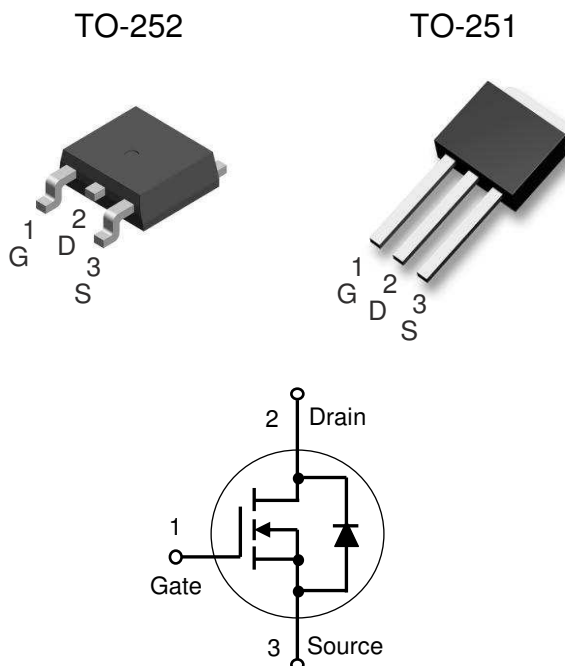
- Low On-State Resistance
- Fast Switching
- Low Gate Charge & Low C_{RSS}
- Fully Characterized Avalanche Voltage and Current
- Specially Designed for AC Adapter, Battery Charger and SMPS
- In compliance with EU RoHs 2002/95/EC Directives

Mechanical Information

- Case: TO-252 / TO-251 Molded Plastic
- Terminals : Solderable per MIL-STD-750, Method 2026

Marking & Ordering Information

TYPE	MARKING	PACKAGE	PACKING
HY2N65D	2N65D	TO-252	2500PCS/REEL
HY2N65M	2N65M	TO-251	70PCS/TUBE



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	HY2N65D	HY2N65M	Units
Drain-Source Voltage		V_{DS}	650		V
Gate-Source Voltage		V_{GS}	± 30		V
Continuous Drain Current	$T_c=25^\circ\text{C}$	I_D	2	2	A
Pulsed Drain Current ¹⁾		I_{DM}	8	8	A
Maximum Power Dissipation	$T_c=25^\circ\text{C}$	P_D	43.8	43	W
Derating Factor			0.35	0.35	
Avalanche Energy with Single Pulse $I_{AS}=2A, V_{DD}=60V, L=50mH$		E_{AS}	100		mJ
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +150		$^\circ\text{C}$

Note : 1. Maximum DC current limited by the package

Thermal Characteristics

Parameter	Symbol	HY2N65D	HY2N65M	Units
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	2.85	2.9	$^\circ\text{C/W}$
Junction-to-Air Thermal Resistance	$R_{\theta JA}$	50	110	$^\circ\text{C/W}$

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Electrical Characteristics ($T_c=25^{\circ}\text{C}$, Unless otherwise noted)

Paramter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V 、 I _D =250uA	650	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} 、 I _D =250uA	2.0	-	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V 、 I _D =1A	-	4.1	4.6	Ω
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =650V 、 V _{GS} =0V	-	-	10	uA
Gate Body Leakage Current	I _{GSS}	V _{GS} =±30V 、 V _{DS} =0V	-	-	±100	nA
Dynamic						
Total Gate Charge	Qg	V _{DS} =520V 、 I _D =2A V _{GS} =10V	-	6.4	8.6	nC
Gate-Source Charge	Qgs		-	1.8	-	
Gate-Drain Charge	Qgd		-	2.1	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} =325V 、 I _D =2A V _{GS} =10V 、 R _G =25Ω	-	13.2	16	ns
Turn-On Rise Time	t _r		-	18.6	28	
Turn-Off Delay Time	t _{d(off)}		-	22	38	
Turn-Off Fall Time	t _f		-	16.8	32	
Input Capacitance	C _{iss}	V _{DS} =25V 、 V _{GS} =0V f=1.0M _{HZ}	-	265	-	pF
Output Capacitance	C _{oss}		-	36	-	
Reverse Transfer Capacitance	C _{rss}		-	1.5	-	
Source-Drain Diode						
Max. Diode Forwad Voltage	I _S	-	-	-	2.0	A
Max. Pulsed Source Current	I _{SM}	-	-	-	8.0	A
Diode Forward Voltage	V _{SD}	I _S =2A 、 V _{GS} =0V	-	-	1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} =0V 、 I _S =2A di/dt=100A/us	-	190	-	ns
Reverse Recovery Charge	Q _{rr}		-	1.0	-	uC

NOTE : Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$

Typical Characteristics Curves ($T_C=25^\circ\text{C}$, unless otherwise noted)

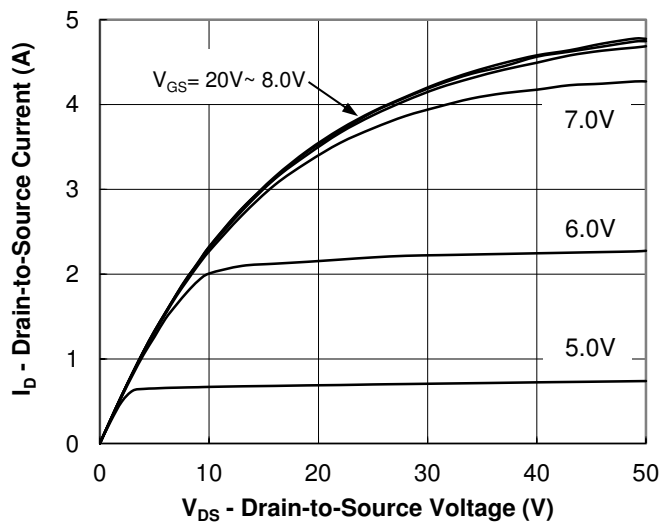


Fig.1 Output Characteristic

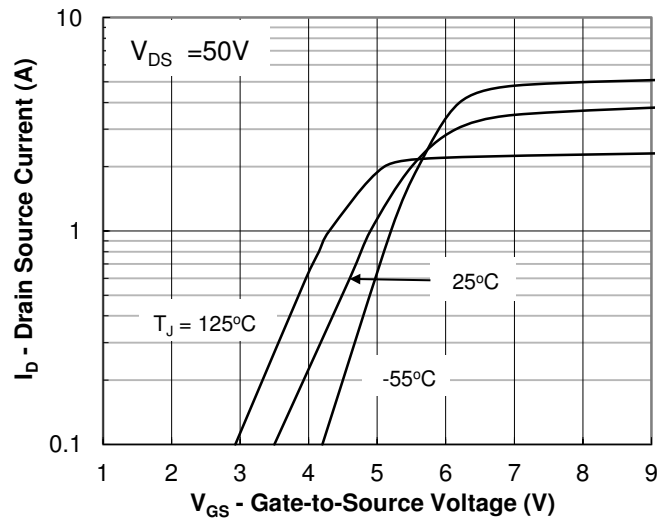


Fig.2 Transfer Characteristic

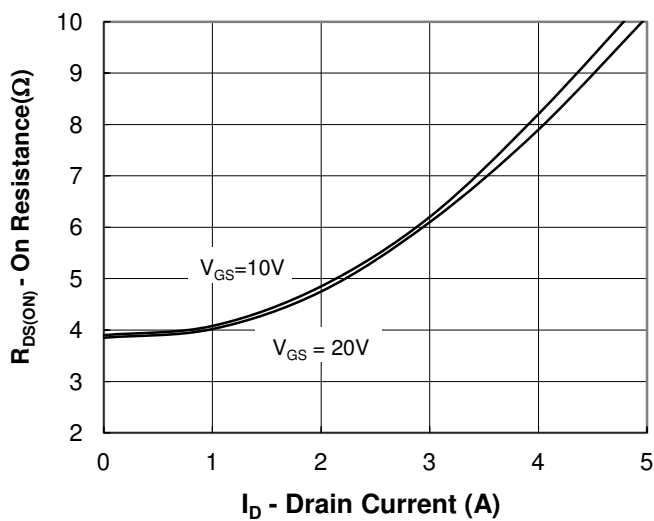


Fig.3 On-Resistance vs Drain Current

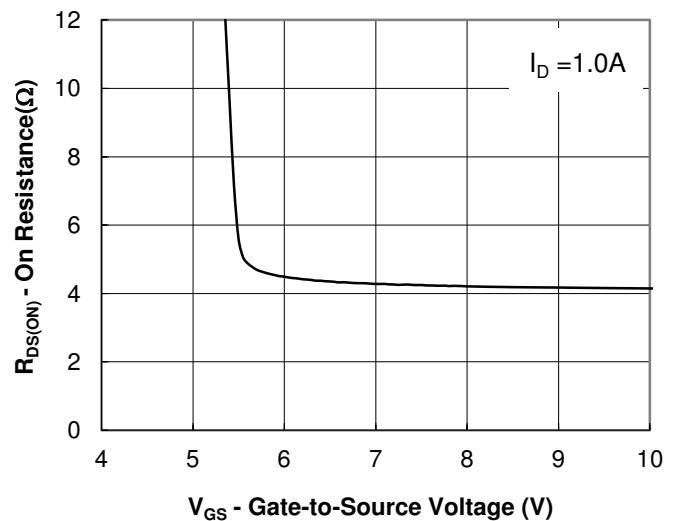


Fig.4 On-Resistance vs Gate to Source Voltage

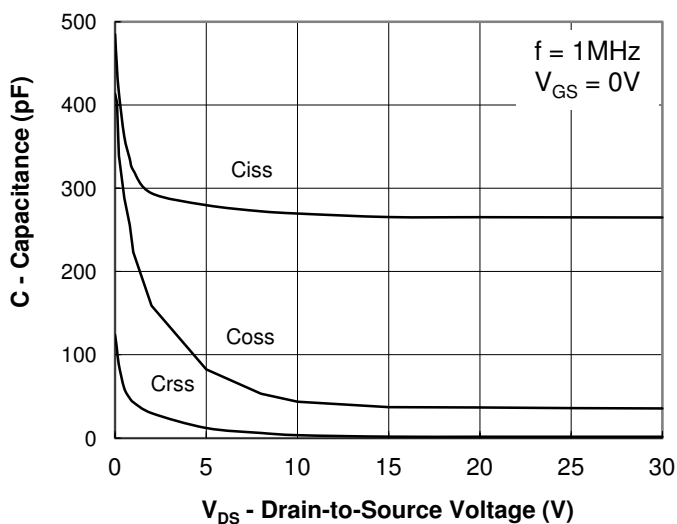


Fig.5 Capacitance Characteristic

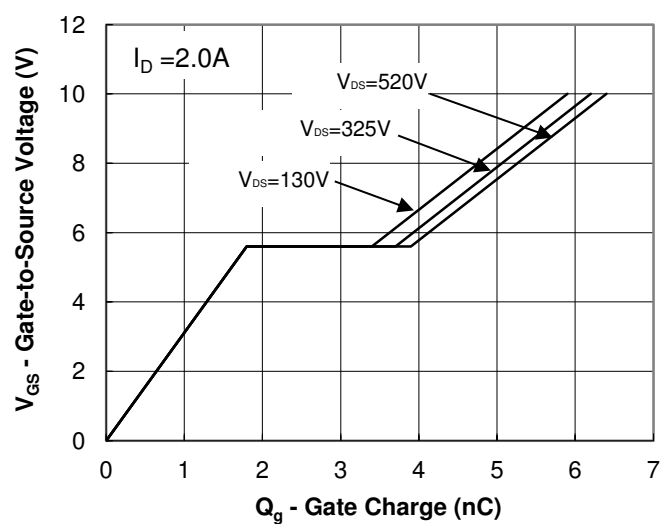


Fig.6 Gate Charge Characteristic

Typical Characteristics Curves ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

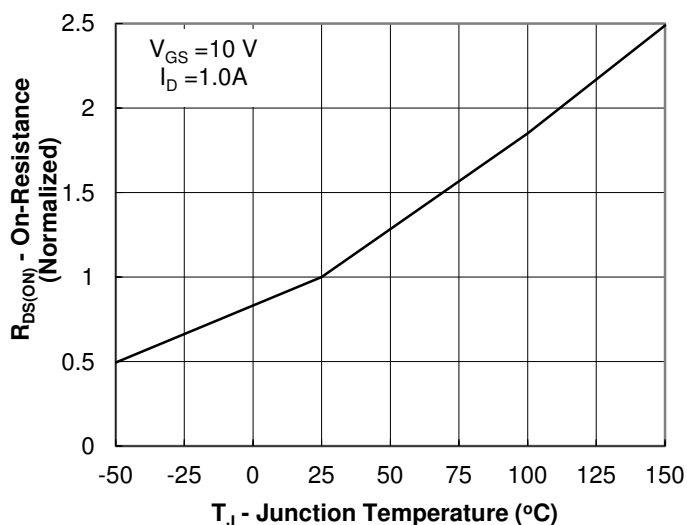


Fig.7 On-Resistance vs Junction Temperature

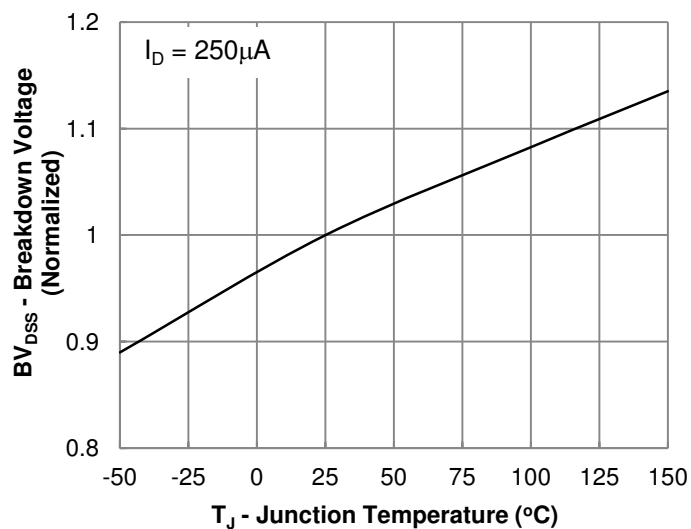


Fig.8 Breakdown Voltage vs Junction Temperature

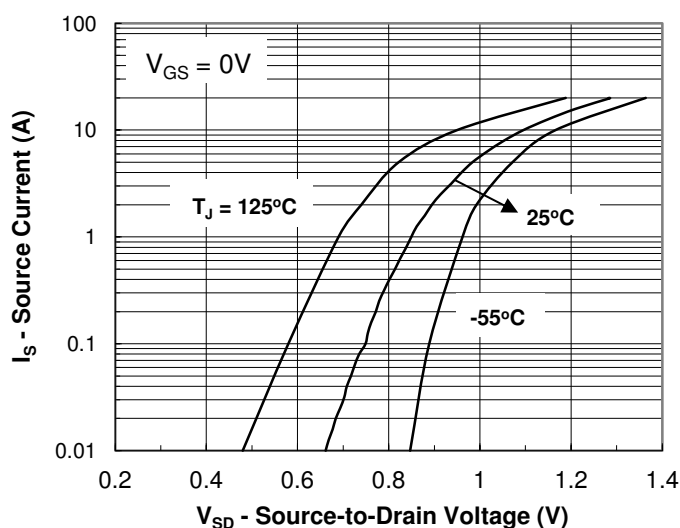


Fig.9 Body Diode Forward Voltage Characteristic